

Single Micropower, Chopper Stabilized, RRIO Operational Amplifier

ISL28133

The ISL28133 is a single micropower, chopper stabilized operational amplifier that is optimized for single supply operation from 1.65V to 5.5V. Its low supply current of $18\mu A$ and wide input range enable the ISL28133 to be an excellent general purpose op amp for a range of applications. The ISL28133 is ideal for handheld devices that operates off 2 AA or single Li-ion batteries.

The ISL28133 is available in the 5 Ld SOT-23, the 5 Ld SC70 and the 6 Ld 1.6mmx1.6mm μ TDFN packages. All devices operates over the extended temperature range of -40°C to +125°C.

Features

• Low Input Offset Voltage δμν, Max.
• Low Offset TC 0.075μV/°C, Max
• Input Bias Current 300pA, Max.
• Quiescent Current 18µA, Typ.
• Wide Supply Range 1.65V to 5.5V
• Low Noise (0.01Hz to 10Hz)1.1 μ V _{P-P} , Typ.
 Rail-to-Rail Inputs and Output
• Operating Temperature Range40°C to +125°C

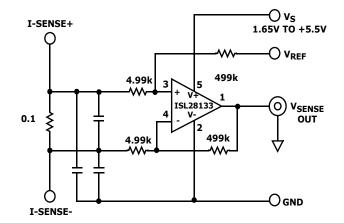
Applications*(see page 17)

- Bidirectional Current Sense
- Temperature Measurement
- Medical Equipment
- Electronic Weigh Scales

Related Literature

- AN1480 "ISL28133ISENS-EV1Z Evaluation Board Users Guide"
- AN1499 "ISL28133EVAL1Z High Gain Evaluation Board User's Guide"

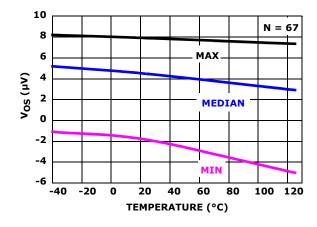
Typical Application



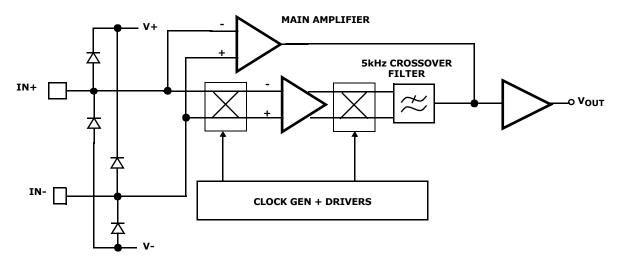
BIDIRECTIONAL CURRENT SENSE AMPLIFIER

1

V_{OS} vs Temperature



Block Diagram



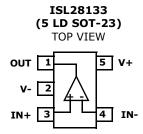
Ordering Information

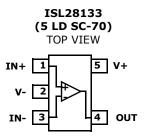
PART NUMBER	PART MARKING	PACKAGE (Pb-Free)	PKG. DWG. #		
ISL28133FHZ-T7 (Notes 1, 2)	BCFA	5 Ld SOT-23	MDP0038		
ISL28133FEZ-T7 (Notes 1, 2)	ВНА	5 Ld SC70	P5.049		
ISL28133FRUZ-T7 (Notes 1, 3)	Т8	6 Ld μTDFN	L6.1.6x1.6		
ISL28133ISENS-EV1Z	Evaluation Board				
ISL28133EVAL1Z	Evaluation Board				

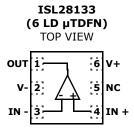
NOTES:

- 1. Please refer to TB347 for details on reel specifications.
- 2. These Intersil Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pbfree requirements of IPC/JEDEC J STD-020.
- 3. These Intersil Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- 4. For Moisture Sensitivity Level (MSL), please see device information page for ISL28133. For more information on MSL please see techbrief TB363.

Pin Configuration







Pin Descriptions

ISL28133 (5 Ld SOT23)	ISL28133 (5 Ld SC70)	ISL28133 (6 Ld µTDFN)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
3	1	4	IN+	Non-inverting input	IN- CLOCK GEN + DRIVERS
					Circuit 1
2	2	2	V-	Negative supply	
4	3	3	IN-	Inverting input	(See Circuit 1)
1	4	1	OUT	Output	V+ OUT Circuit 2
5	5	6	V+	Positive supply	
		5	NC	Not Connected -	This pin is not electrically connected internally.

Absolute Maximum Ratings

Max Supply Voltage V+ to V6.5V
Max Voltage VIN to GND0.5V to 6.5V
Max Input Differential Voltage 6.5V
Max Input Current 20mA
Max Voltage VOUT to GND (10s) 6.5V
ESD Rating
Human Body Model
Machine Model
Charged Device Model

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)
5 Ld SOT-23 (Notes 5)	225
5 Ld SC70 (Notes 5)	206
6 Ld μTDFN (Notes 5)	240
Maximum Storage Temperature Range65°0	C to +150°C
Pb-Free Reflow Profile se	e link below
http://www.intersil.com/pbfree/Pb-FreeReflov	v.asp

Operating Conditions

Temperature Range	-40°C to +125°C
Maximum Junction Temperature	140°C

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTE

5. θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

Electrical Specifications $V_+ = 5V$, $V_- = 0V$, VCM = 2.5V, $T_A = +25$ °C, $R_L = Open$, unless otherwise specified. Boldface limits apply over the operating temperature range, -40°C to +125°C.

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 6)	ТҮР	MAX (Note 6)	UNIT
DC SPECIFICATION	IS			•		
V _{OS}	Input Offset Voltage		-8	±2	8	μV
			-15.5		15.5	μV
TCV _{OS}	Input Offset Voltage Temperature Coefficient			0.02	0.075	μV/°C
I _{OS}	Input Offset Current			-60		pА
I _B	Input Bias Current		-300	±30	300	pA
			-600		600	pA
Common Mode Input Voltage Range		V+ = 5.0V, V- = GND	-0.1		5.1	V
CMRR	Common Mode Rejection Ratio	VCM = -0.1V to 5.0V	118	125		dB
			115			dB
PSRR	Power Supply Rejection Ratio	Vs = 2V to 5.5V	110	138		dB
			110			dB
V _{OH}	Output Voltage Swing, High	$R_L = 10k\Omega$	4.965	4.981		V
V _{OL}	Output Voltage Swing, Low	$R_L = 10k\Omega$		18	35	mV
A _{OL}	Open Loop Gain	$R_L = 1M\Omega$		174		dB
V ₊	Supply Voltage	(Note 7)	1.65		5.5	V
I_{S}	Supply Current	$R_L = OPEN$		18	25	μΑ
					35	μΑ
I _{SC+}	Output Source Short Circuit Current	R _L = Short to ground or V+	13	17	26	mA
I _{SC-}	Output Sink Short Circuit Current		-26	-19	-13	mA
AC SPECIFICATION	IS					
GBWP	Gain Bandwidth Product f = 50kHz	$\begin{aligned} &A_{V} = 100, R_{F} = 100 k\Omega, \\ &R_{G} = 1 k\Omega, R_{L} = 10 k\Omega to V_{CM} \end{aligned}$		400		kHz
e _N V _{P-P}	Peak-to-Peak Input Noise Voltage	f = 0.01Hz to 10Hz		1.1		μV_{P-P}

intersil

Electrical Specifications $V_+ = 5V$, $V_- = 0V$, VCM = 2.5V, $T_A = +25$ °C, $R_L = Open$, unless otherwise specified. **Boldface** limits apply over the operating temperature range, -40°C to +125°C. (Continued)

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 6)	ТҮР	MAX (Note 6)	UNIT
e _N	Input Noise Voltage Density	f = 1kHz		65		nV/√(Hz)
i _N	Input Noise Current Density	f = 1kHz		72		fA/√(Hz)
		f = 10Hz		79		fA/√(Hz)
C _{in}	Differential Input Capacitance	f = 1MHz		1.6		pF
	Common Mode Input Capacitance			1.12		pF
TRANSIENT RESP	ONSE		1		•	
SR	Positive Slew Rate	V_{OUT} = 1V to 4V, R_L = 10k Ω		0.2		V/µs
	Negative Slew Rate			0.1		V/µs
t _r , t _f , Small Signal	Rise Time, t _r 10% to 90%	$A_V = +1$, $V_{OUT} = 0.1V_{P-P}$,		1.1		μs
	Fall Time, t _f 10% to 90%	$R_F = 0\Omega, R_L = 10k\Omega,$ $C_L = 1.2pF$		1.1		μs
t _r , t _f Large Signal	Rise Time, t _r 10% to 90%	$A_V = +1, V_{OUT} = 2V_{P-P},$		8		μs
	Fall Time, t _f 10% to 90%	$R_F = 0\Omega, R_L = 10k\Omega,$ $C_L = 1.2pF$		10		μs
t _s	Settling Time to 0.1%, 2V _{P-P} Step	$A_V = +1, R_F = 0\Omega, \\ R_L = 10k\Omega, C_L = 1.2pF$		35		μs

NOTES:

- 6. Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.
- 7. Parts are 100% tested with a minimum operating voltage of 1.65V to a VOS limit of $\pm 15 \mu V$.

Typical Performance Curves V+=5V, V-=0V, $V_{CM}=2.5V$, $R_L=Open$.

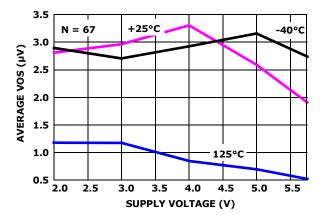


FIGURE 1. AVERAGE INPUT OFFSET VOLTAGE vs SUPPLY VOLTAGE

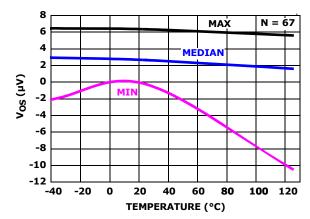
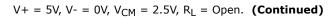


FIGURE 2. V_{OS} vs TEMPERATURE, $V_S = \pm 1.0V$, $V_{IN} = 0V$, $R_L = INF$



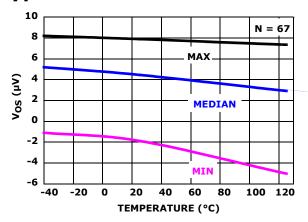


FIGURE 3. V_{OS} vs TEMPERATURE, $V_S = \pm 2.5V$, $V_{IN} = 0V$, $R_L = INF$

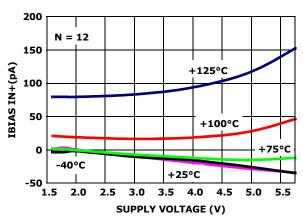


FIGURE 4. I_B+ vs SUPPLY VOLTAGE vs TEMPERATURE

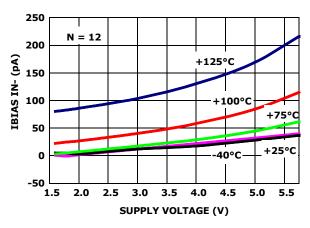


FIGURE 5. I_B - vs SUPPLY VOLTAGE vs TEMPERATURE

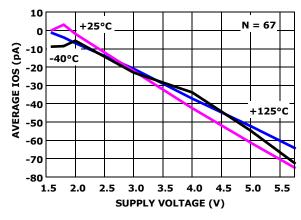


FIGURE 6. IOS vs SUPPLY VOLTAGE vs TEMPERATURE

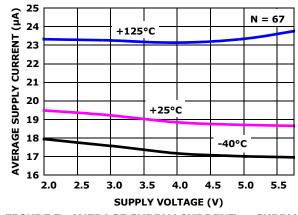
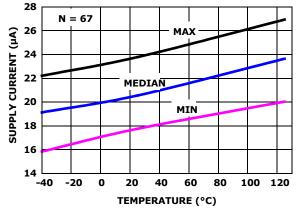


FIGURE 7. AVERAGE SUPPLY CURRENT vs SUPPLY VOLTAGE



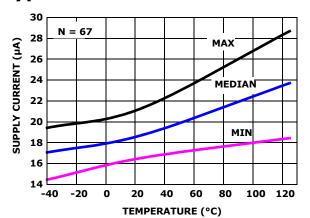


FIGURE 9. MIN/MAX SUPPLY CURRENT vs TEMPERATURE, $V_S = \pm 2.5 V$, $V_{IN} = 0 V$, $R_L = INF$

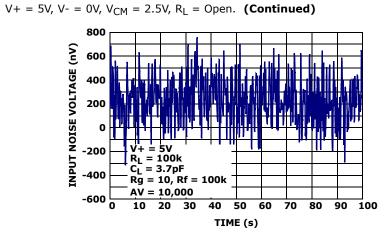


FIGURE 10. INPUT NOISE VOLTAGE 0.01Hz TO 10Hz

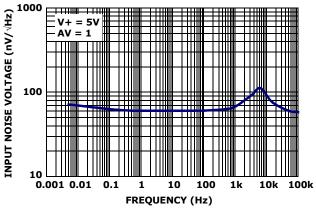


FIGURE 11. INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

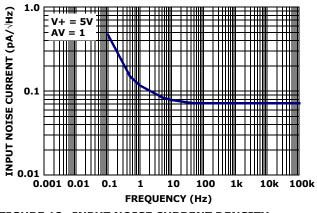


FIGURE 12. INPUT NOISE CURRENT DENSITY vs FREQUENCY

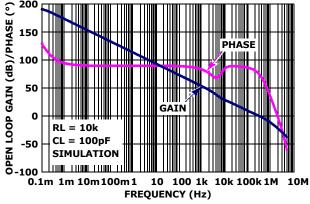


FIGURE 13. FREQUENCY RESPONSE vs OPEN LOOP GAIN, $R_L = 10k$

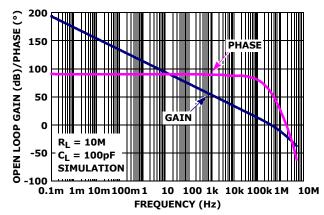
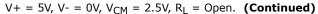


FIGURE 14. FREQUENCY RESPONSE vs OPEN LOOP GAIN, $R_L = 10M$



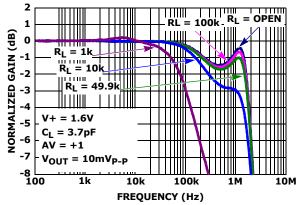


FIGURE 15. GAIN vs FREQUENCY vs R_{L_1} $V_S = 1.6V$

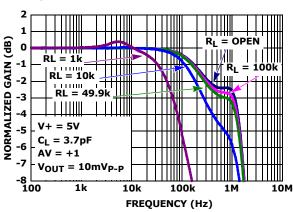


FIGURE 16. GAIN vs FREQUENCY vs R_L , $V_S = 5V$

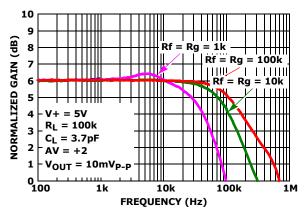


FIGURE 17. GAIN vs FREQUENCY vs FEEDBACK RESISTOR VALUES R_f/R_g

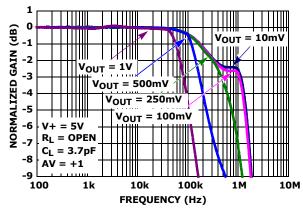


FIGURE 18. GAIN vs FREQUENCY vs V_{OUT} , $R_L = OPEN$

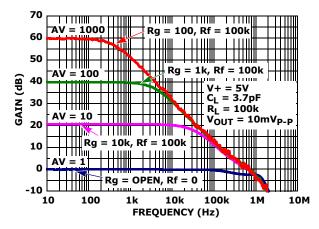


FIGURE 19. FREQUENCY RESPONSE vs CLOSED LOOP GAIN

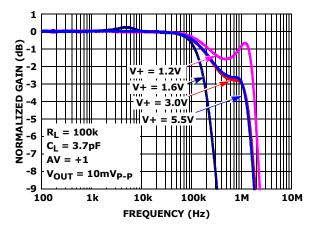
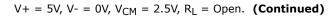


FIGURE 20. GAIN vs FREQUENCY vs SUPPLY VOLTAGE



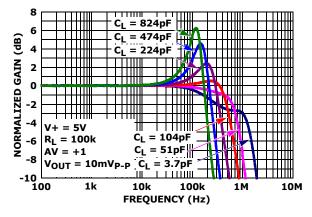


FIGURE 21. GAIN vs FREQUENCY vs CL

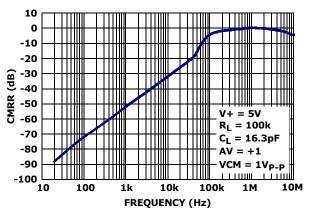


FIGURE 22. CMRR vs FREQUENCY, $V_S = 5V$

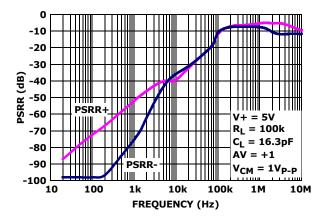


FIGURE 23. PSRR vs FREQUENCY, $V_S = 5V$

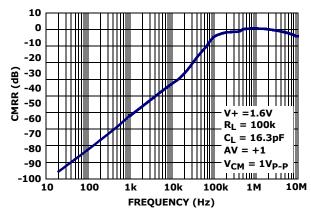


FIGURE 24. CMRR vs FREQUENCY, V_S = 1.6V

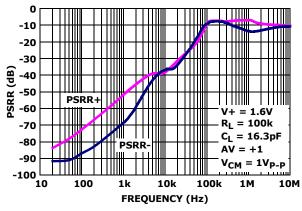


FIGURE 25. PSRR vs FREQUENCY, $V_S = 1.6V$

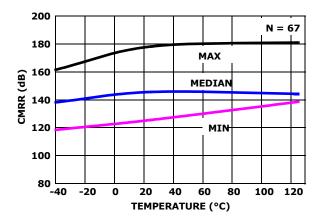


FIGURE 26. CMRR vs TEMPERATURE, VCM = -2.5V TO +2.5V, V+ = $\pm 2.5V$

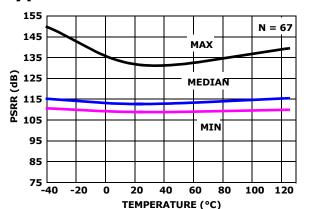


FIGURE 27. PSRR vs TEMPERATURE, V+ = 2V TO 5.5V

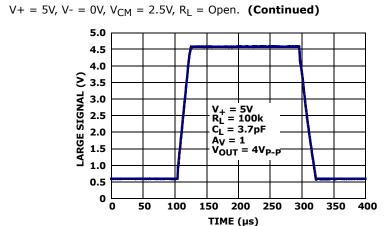


FIGURE 28. LARGE SIGNAL STEP RESPONSE (4V)

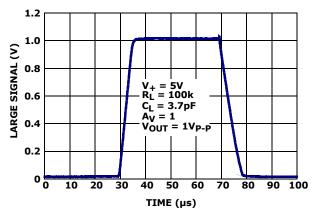


FIGURE 29. LARGE SIGNAL STEP RESPONSE (1V)

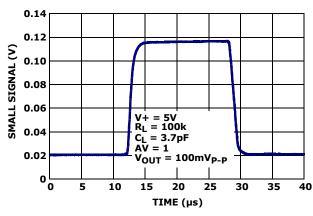


FIGURE 30. SMALL SIGNAL STEP RESPONSE (100mV)

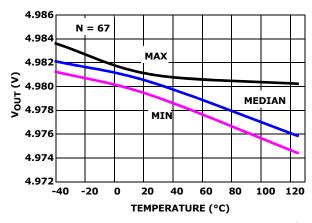


FIGURE 31. V_{OUT} HIGH vs TEMPERATURE, R_L = 10k, V_S +-2.5V

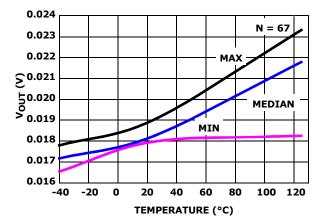


FIGURE 32. V_{OUT} LOW vs TEMPERATURE, $R_L = 10k$, $V_S +-2.5V$

Applications Information

Functional Description

The ISL28133 uses a proprietary chopper-stabilized architecture shown in the "Block Diagram" on page 2. The ISL28133 combines a 400kHz main amplifier with a very high open loop gain (174dB) chopper stabilized amplifier to achieve very low offset voltage and drift (2 μ V, 0.02 μ V/°C typical) while consuming only 18 μ A of supply current per channel.

This multi-path amplifier architecture contains a time continuous main amplifier whose input DC offset is corrected by a parallel-connected, high gain chopper stabilized DC correction amplifier operating at $100 \, \text{kHz}$. From DC to $\sim 5 \, \text{kHz}$, both amplifiers are active with DC offset correction and most of the low frequency gain is provided by the chopper amplifier. A $5 \, \text{kHz}$ crossover filter cuts off the low frequency amplifier path leaving the main amplifier active out to the $400 \, \text{kHz}$ gain-bandwidth product of the device.

The key benefits of this architecture for precision applications are very high open loop gain, very low DC offset, and low 1/f noise. The noise is virtually flat across the frequency range from a few mHz out to 100kHz, except for the narrow noise peak at the amplifier crossover frequency (5kHz).

Rail-to-rail Input and Output (RRIO)

The RRIO CMOS amplifier uses parallel input PMOS and NMOS that enable the inputs to swing 100mV beyond either supply rail. The inverting and non-inverting inputs do not have back-to-back input clamp diodes and are capable of maintaining high input impedance at high differential input voltages. This is effective in eliminating output distortion caused by high slew-rate input signals.

The output stage uses common source connected PMOS and NMOS devices to achieve rail-to-rail output drive capability with 17mA current limit and the capability to swing to within 20mV of either rail while driving a $10 k\Omega$ load.

IN+ and IN- Protection

All input terminals have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode beyond the supply rails. For applications where either input is expected to exceed the rails by 0.5V, an external series resistor must be used to ensure the input currents never exceed 20mA (see Figure 33).

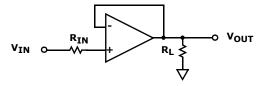


FIGURE 33. INPUT CURRENT LIMITING

Layout Guidelines for High Impedance Inputs

To achieve the maximum performance of the high input impedance and low offset voltage of the ISL28133 amplifiers, care should be taken in the circuit board layout. The PC board surface must remain clean and free of moisture to avoid leakage currents between adjacent traces. Surface coating of the circuit board will reduce surface moisture and provide a humidity barrier, reducing parasitic resistance on the board.

High Gain, Precision DC-Coupled Amplifier

The circuit in Figure 34 implements a single-stage, 10kV/V DC-coupled amplifier with an input DC sensitivity of under 100nV that is only possible using a low VOS amplifier with high open loop gain. This circuit is practical down to 1.8V due to it's rail-to-rail input and output capability. Standard high gain DC amplifiers operating from low voltage supplies are not practical at these high gains using typical low offset precision op amps because the input offset voltage and temperature coefficient consume most of the available output voltage swing. For example, a typical precision amplifier in a gain of 10kV/V with a ±100µV VOS and a temperature coefficient of $0.5\mu V/^{\circ}C$ would produce a DC error at the output of >1V with an additional 5mV°C of temperature dependent error. At 3V, this DC error consumes > 30% of the total supply voltage, making it impractical to measure sub-microvolt low frequency signals.

The $\pm 8\mu V$ max V_{OS} and $0.075\mu V/^{\circ}C$ of the ISL28133 produces a temperature stable maximum DC output error of only $\pm 80mV$ with a maximum temperature drift of $0.75mV/^{\circ}C$. The additional benefit of a very low 1/f noise corner frequency and some feedback filtering enables DC voltages and voltage fluctuations well below 100nV to be easily detected with a simple single stage amplifier.

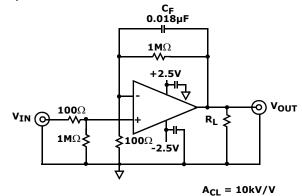


FIGURE 34. HIGH GAIN, PRECISION DC-COUPLED

11

ISL28133 SPICE Model

Figure 35 shows the SPICE model schematic and Figure 36 shows the net list for the ISL28133 SPICE model. The model is a simplified version of the actual device and simulates important parameters such as noise, **Slew Rate,** Gain and Phase. The model uses typical parameters from the ISL28133. The poles and zeros in the model were determined from the actual open and closed-loop gain and phase response. This enables the model to present an accurate AC representation of the actual device. The model is configured for ambient temperature of $+25^{\circ}\text{C}$.

Figures 37 through 44 show the characterization vs simulation results for the Noise Density, Frequency Response vs Close Loop Gain, Gain vs Frequency vs CL and Large Signal Step Response (4V).

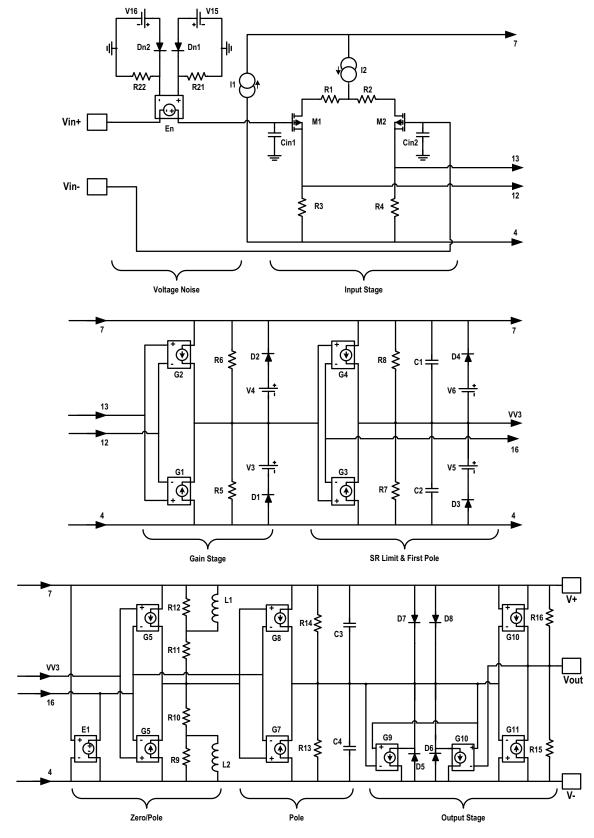


FIGURE 35. SPICE CIRCUIT SCHEMATIC

ISL28133

```
* ISL28133 Macromodel
                                                           V_V6
                                                                    18 VV3 0.7Vdc
* Revision B, April 2009
                                                          *Zero/Pole
* AC characteristics, Voltage Noise
* Connections:
                     +input
                                                           E E1
                                                                    16 4 7 4 0.5
                          -input
                                                           G G5
                                                                    4 VV4 VV3 16 0.000001
                               +Vsupply
                                                           G G6
                                                                    7 VV4 VV3 16 0.000001
                                                                    20 7 0.3H
                                    -Vsupply
                                                          L L1
                                                           R R12
                                                                     20 7 2.5meg
                                         output
                                                           R R11
                                                                     VV4 20 1meg
.subckt ISL28133
                          2
                                          6
                                                           L_L2
                                                                    4 19 0.3H
                                                           R_R9
                                                                    4 19 2.5meg
*Voltage Noise
                                                           R R10
                                                                     19 VV4 1meg
D DN1
           102 101 DN
                                                           *Pole
D DN2
           104 103 DN
                                                           G G7
                                                                    4 VV5 VV4 16 0.000001
R R21
           0 101 120k
                                                           G G8
                                                                    7 VV5 VV4 16 0.000001
                                                                    VV5 7 0.12p
R R22
          0 103 120k
                                                           C C3
E_EN
          8 3 101 103 1
                                                          C_C4
                                                                    4 VV5 0.12p
V V15
          102 0 0.1Vdc
                                                          R R13
                                                                     4 VV5 1meg
V_V16
          104 0 0.1Vdc
                                                           R_R14
                                                                     VV5 7 1meg
*Input Stage
                                                           *Output Stage
C_Cin1
           80 0.4p
                                                           G G9
                                                                     21 4 6 VV5 0.0000125
C_Cin2
                                                          G_G10
           20 2.0p
                                                                     22 4 VV5 6 0.0000125
         9 10 10
                                                                    4 21 DY
R R1
                                                          D D5
R R2
         10 11 10
                                                           D D6
                                                                    4 22 DY
R R3
                                                           D D7
         4 12 100
                                                                    7 21 DX
R R4
         4 13 100
                                                           D D8
                                                                    7 22 DX
M M1
          12899 pmosisil
                                                           R R15
                                                                     46 8k
+ L=50u
                                                           R R16
                                                                     67 8k
+ W=50u
                                                          G G11
                                                                      6 4 VV5 4 -0.000125
M M2
          13 2 11 11 pmosisil
                                                           G_G12
                                                                      7 6 7 VV5 -0.000125
+ L=50u
+ W=50u
                                                           .model pmosisil pmos (kp=16e-3 vto=10m)
1 11
        4 7 DC 92uA
                                                           .model DN D(KF=6.4E-16 AF=1)
I_I2
        7 10 DC 100uA
                                                           .MODEL DX D(IS=1E-18 Rs=1)
                                                           .MODEL DY D(IS=1E-15 BV=50 Rs=1)
*Gain stage
                                                           .ends ISL28133
G G1
         4 VV2 13 12 0.0002
G G2
         7 VV2 13 12 0.0002
R R5
         4 VV2 1.3Meg
R R6
         VV2 7 1.3Meg
D D1
         4 14 DX
D D2
         15 7 DX
V V3
         VV2 14 0.7Vdc
V_V4
         15 VV2 0.7Vdc
*SR limit first pole
         4 VV3 VV2 16 1
G G3
G G4
          7 VV3 VV2 16 1
R R7
         4 VV3 1meg
R R8
         VV3 7 1meg
C C1
         VV3 7 12u
C_C2
         4 VV3 12u
D D3
         4 17 DX
D D4
         18 7 DX
V V5
         VV3 17 0.7Vdc
```

FIGURE 36. SPICE NET LIST

Characterization vs Simulation Results

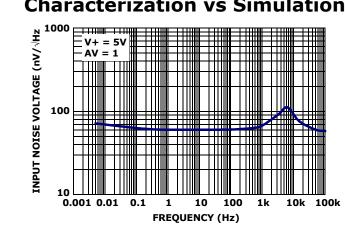


FIGURE 37. CHARACTERIZED INPUT NOISE VOLTAGE **DENSITY vs FREQUENCY**

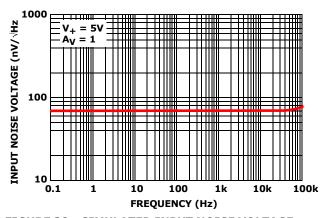


FIGURE 38. SIMULATED INPUT NOISE VOLTAGE **DENSITY vs FREQUENCY**

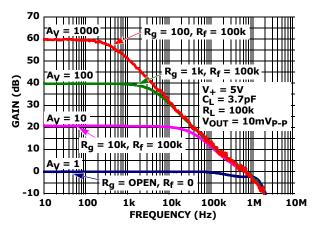


FIGURE 39. CHARACTERIZED FREOUENCY RESPONSE **vs CLOSED LOOP GAIN**

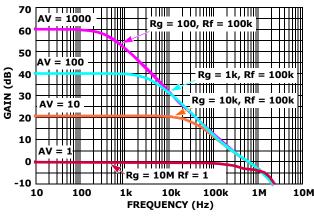


FIGURE 40. SIMULATED FREQUENCY RESPONSE vs **CLOSED LOOP GAIN**

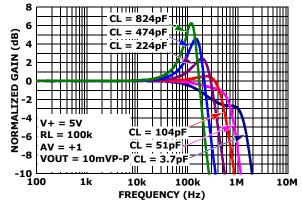


FIGURE 41. CHARACTERIZED GAIN vs FREQUENCY vs C_L

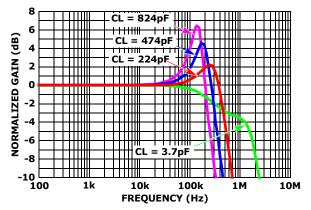


FIGURE 42. SIMULATED GAIN vs FREQUENCY vs C₁

Characterization vs Simulation Results (Continued)

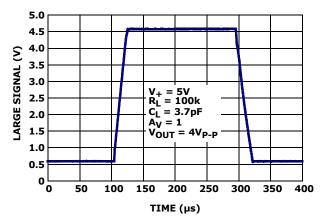


FIGURE 43. CHARACTERIZED LARGE SIGNAL STEP RESPONSE (4V)

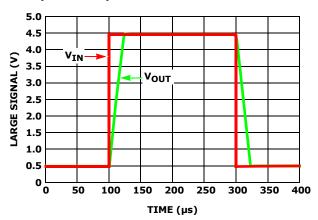


FIGURE 44. SIMULATED LARGE SIGNAL STEP RESPONSE (4V)

Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

DATE	REVISION	CHANGE
5/3/10	FN6560.3	Title Page 1: Replaced "Zero-Drift" with "Chopper Stabilized" for title and part description On page 3: Pin Configuration: MTDFN -> uTDFN On page 7: Figure 10: Changed 0.1Hz to 0.01Hz in Figure caption On page 11: In "Functional Description"; Paragraph 1, 2nd sentence: Changed text from "open loop gain (200dB)" -to- "open loop gain (174dB)" Changed TYP for "Open Loop Gain" on page 4 from 200dB to 174dB. On page 11: In "High Gain, Precision DC-Coupled Amplifier"; Paragraph 2, 1st sentence: Changed text from "DC output error of only ±80mV with a maximum temperature drift of 0.75μV/°C." to " DC output error of only ±80mV with a maximum temperature drift of 0.75mV/C."
2/24/10		Removed "Coming Soon" from ISL28133EVAL1Z in the ordering information table on pg 2.
09/24/09	FN6560.2	Converted to new Intersil template. Removed ISL28233 and ISL28433 from data sheet, added Applications, Related Literature, Typical Application Circuit, Performance Curve, updated ordering information by removing "coming soon" on SC70 and uTDFN packages and adding Eval board listed as "coming soon". Added Block Diagram, Changed in Abs Max Rating Voltage from "5.75V" to "6.5V". Removed Tjc from Thermal Information until provided by packaging scheduled for 9-11-09. Changed Low Offset "drift" to Low Offset "TC", added Max Junction Temp 140C, added SPICE model and simulation results, removed supply current graph at +-3V, re-ordered typical performance curves, removed guard ring information from application section. Added Revision History and Products Information
05/29/09	FN6560.1	Page 4: Removed the RL = 100 Curve from Figures 3, 4 and 5. Page 1: Under Features, removed the word "Output" from "Low Output Noise"
03/25/09	FN6560.0	Initial Release to WEB

Products

Intersil Corporation is a leader in the design and manufacture of high-performance analog semiconductors. The Company's products address some of the industry's fastest growing markets, such as, flat panel displays, cell phones, handheld products, and notebooks. Intersil's product families address power management and analog signal processing functions. Go to www.intersil.com/products for a complete list of Intersil product families.

*For a complete listing of Applications, Related Documentation and Related Parts, please see the respective device information page on intersil.com: ISL28133

To report errors or suggestions for this data sheet, please go to www.intersil.com/askourstaff

FITs are available from our website at http://rel.intersil.com/reports/search.php

Small Outline Transistor Plastic Packages (SC70-5)

VIEW C Ε ፍ ፍ 3 b 0.20 (0.008) M ፍ **SEATING PLANE** -C-0.10 (0.004) C WITH **PLATING 1** c1 **BASE METAL** 4X θ1 - GAUGE PLANE **SEATING PLANE** С 4X θ1 ~ VIEW C → 0.65mm

P5.0495 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE

	INC	HES	MILLIMETERS		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	0.031	0.043	0.80	1.10	-
A1	0.000	0.004	0.00	0.10	-
A2	0.031	0.039	0.80	1.00	-
b	0.006	0.012	0.15	0.30	-
b1	0.006	0.010	0.15	0.25	
С	0.003	0.009	0.08	0.22	6
c1	0.003	0.009	0.08	0.20	6
D	0.073	0.085	1.85	2.15	3
E	0.071	0.094	1.80	2.40	-
E1	0.045	0.053	1.15	1.35	3
е	0.025	0.0256 Ref		Ref	-
e1	0.0512 Ref		1.30	Ref	-
L	0.010	0.018	0.26	0.46	4
L1	0.017	0.017 Ref.		Ref.	-
L2	0.006	0.006 BSC		BSC	
α	0°	8 ⁰	0°	8 ⁰	-
N	ļ	5	Į.	5	5
R	0.004	-	0.10	-	
R1	0.004	0.010	0.15	0.25	0.7/07

Rev. 3 7/07

NOTES:

- 1. Dimensioning and tolerances per ASME Y14.5M-1994.
- 2. Package conforms to EIAJ SC70 and JEDEC MO-203AA.
- 3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.
- 4. Footlength L measured at reference to gauge plane.
- 5. "N" is the number of terminal positions.
- 6. These Dimensions apply to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.
- 7. Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.

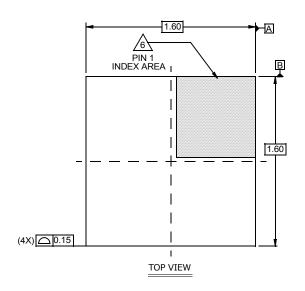
TYPICAL RECOMMENDED LAND PATTERN

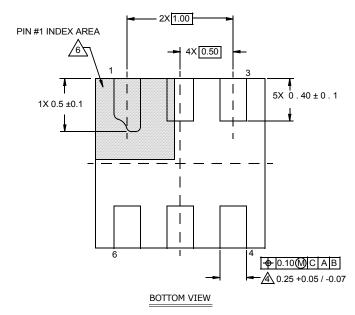
Package Outline Drawing

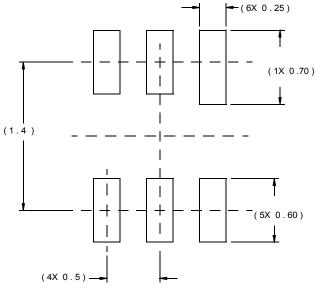
L6.1.6x1.6

6 LEAD ULTRA THIN DUAL FLAT NO-LEAD COL PLASTIC PACKAGE (UTDFN COL)

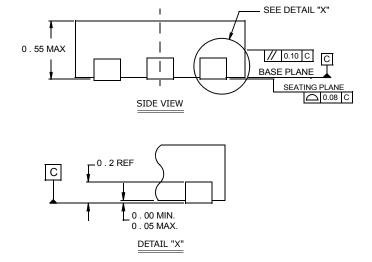
Rev 1, 11/07







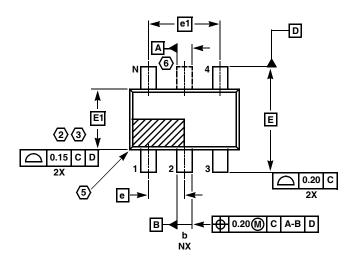
TYPICAL RECOMMENDED LAND PATTERN

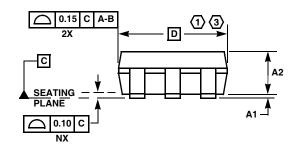


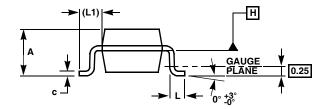
NOTES:

- Dimensions are in millimeters.
 Dimensions in () for Reference Only.
- 2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
- 3. Unless otherwise specified, tolerance : Decimal ± 0.05
- 4. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.
- 5. Tiebar shown (if present) is a non-functional feature.
- The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.

SOT-23 Package Family







MDP0038 SOT-23 PACKAGE FAMILY

	MILLIM		
SYMBOL	SOT23-5	SOT23-6	TOLERANCE
Α	1.45	1.45	MAX
A1	0.10	0.10	±0.05
A2	1.14	1.14	±0.15
b	0.40	0.40	±0.05
С	0.14	0.14	±0.06
D	2.90	2.90	Basic
E	2.80	2.80	Basic
E1	1.60	1.60	Basic
е	0.95	0.95	Basic
e1	1.90	1.90	Basic
L	0.45	0.45	±0.10
L1	0.60	0.60	Reference
N	5	6	Reference

Rev. F 2/07

NOTES:

- Plastic or metal protrusions of 0.25mm maximum per side are not included.
- Plastic interlead protrusions of 0.25mm maximum per side are not included.
- 3. This dimension is measured at Datum Plane "H".
- 4. Dimensioning and tolerancing per ASME Y14.5M-1994.
- Index area Pin #1 I.D. will be located within the indicated zone (SOT23-6 only).
- 6. SOT23-5 version has no center lead (shown as a dashed line).

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